

DCR750D24

Phase Control Thyristor

DS6036-2 June 2019 (LN38856)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR750D24 DCR750D22 DCR750D20	2400 2200 2000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 50\text{mA}, \\ V_{DRM}, V_{RRM} t_p &= 10\text{ms}, \\ V_{DSM} \& V_{RSM} &= \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR750D24

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	2400 V
$I_{T(AV)}$	750 A
I _{TSM}	10000 A
dV/dt*	1000 V/μs
dl/dt	200 A/μs

* Higher dV/dt selections available

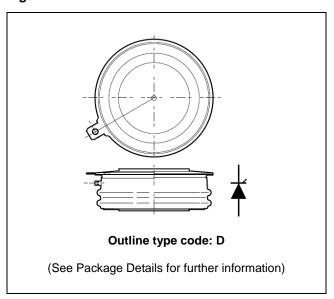


Fig. 1 Package outline



CURRENT RATINGS

$T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions		Units	
Double Si	Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	750	Α	
I _{T(RMS)}	RMS value	-	1180	А	
I _T	Continuous (direct) on-state current	-	1060	Α	

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	10.0	kA
l ² t	I ² t for fusing	$V_R = 0$	0.50	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	1	0.035	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.01	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-40	140	°C
Fm	Clamping force			8	12	kN



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	50	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	1000	-	V/µs
dI/dt	Rate of rise of on-state current	From 67% V _{DRM} to 1000A	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V _T	On-state voltage	I _T = 1500A, T _{case} = 125°C			2.00	V
V _{T(TO)}	Threshold voltage – Low level	T _{case} = 125°C		-	0.92	V
r _T	On-state slope resistance – Low level	T _{case} = 125°C		-	0.72	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3.0	μs
	·	$t_r = 0.5 \mu s, \ T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 10$ A/ μ s,		-	150	μs
		dV _{DR} /dt = 20V/μs linear to 67% V _{DRM}				
Qs	Stored charge	$I_T = 1000A$, $tp = 1000us, T_j = 125°C$, $dI/dt = 10A/\mu s$,		-	2300	μC
I _{RR}	Reverse recovery current			-	125	Α
l _L	Latching current	T _j = 25°C,		-	1	Α
l _Η	Holding current	T _j = 25°C,		-	200	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter Test Conditions		Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	3	V
V_{GD}	Gate non-trigger voltage	At 40% V _{DRM} , T _{case} = 125°C	0.3	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	300	mA
I _{GD}	Gate non-trigger current	At 40% V _{DRM} , T _{case} = 125°C	20	mA



CURVES

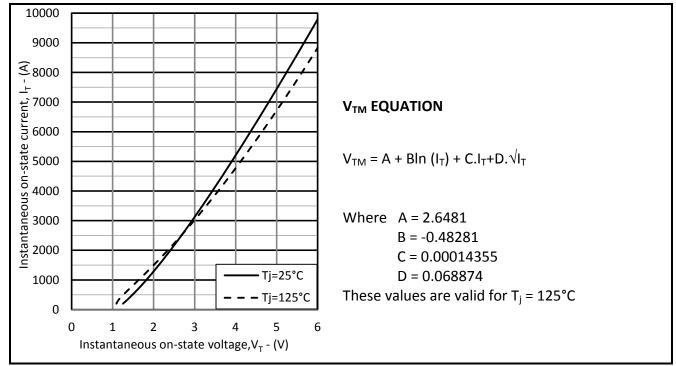


Fig.2 Maximum &minimum on-state characteristics

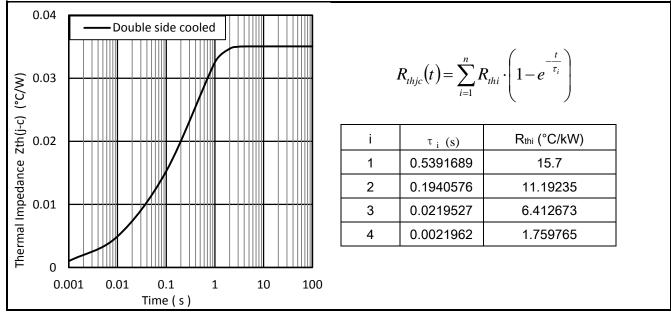
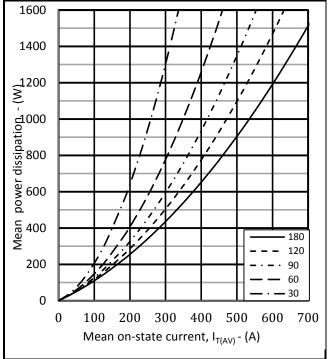
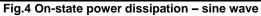


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)







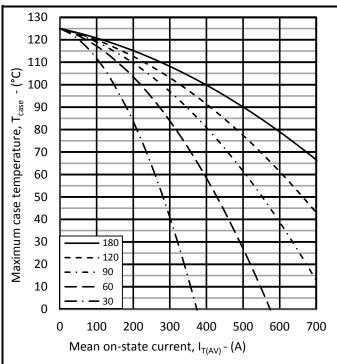


Fig.5 Maximum permissible case temperature, double side cooled – sine wave

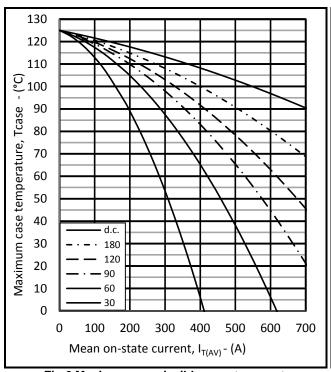


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

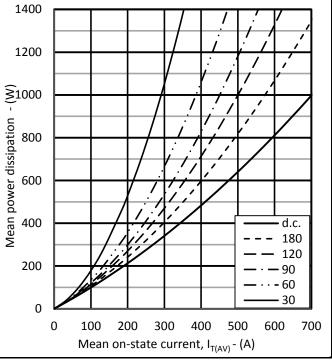
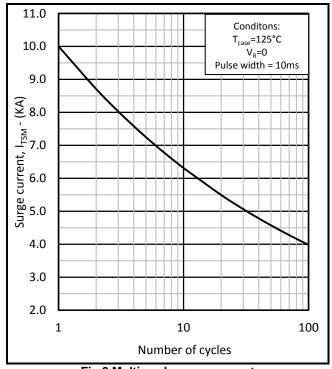
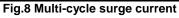


Fig.7 On-state power dissipation - rectangular wave







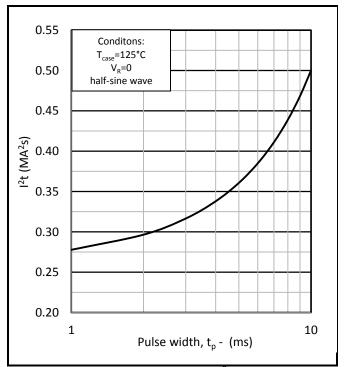


Fig.9 Single-cycle I²t

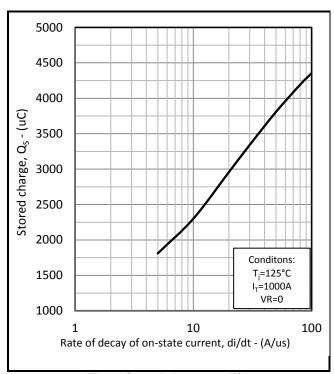


Fig.10 Stored charge vs di/dt

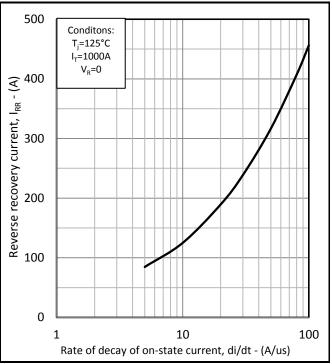


Fig.11 Reverse recovery current vs di/dt



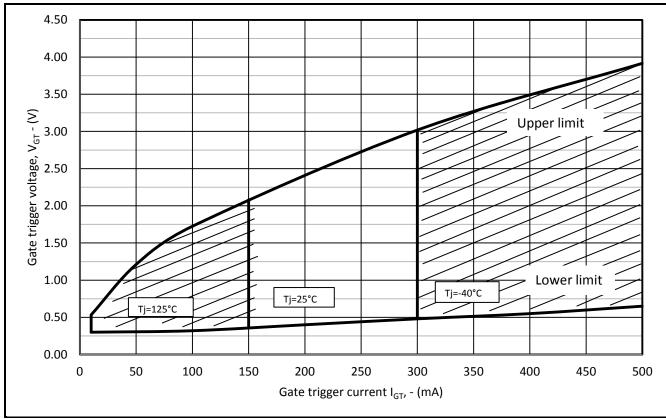


Fig.12 Gate characteristics

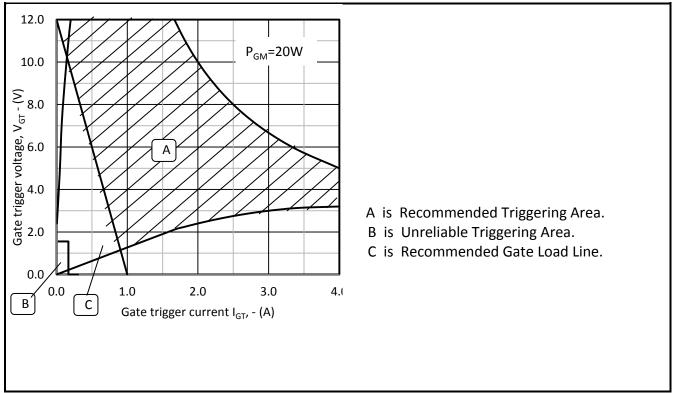


Fig.13 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

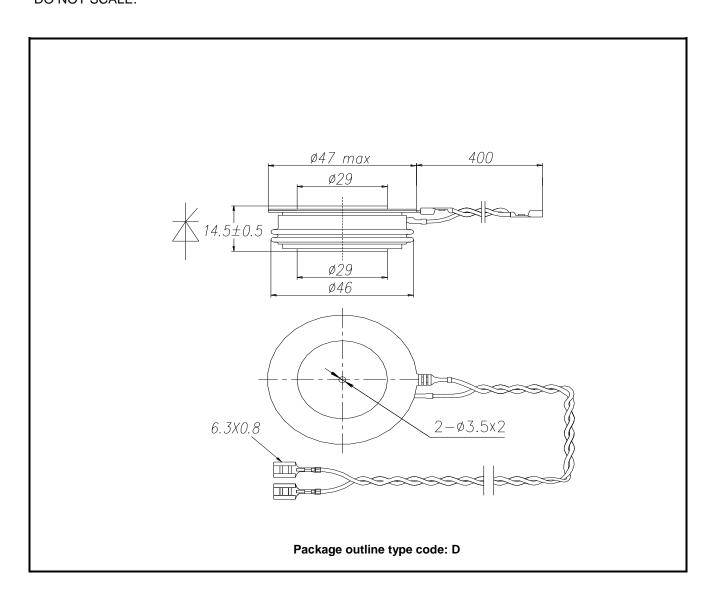


Fig.14 Package outline



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No actual design work on the product has been started.

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